

Application No.: 10/660,779  
Amendment dated: June 10, 2005  
Reply to Final Office Action of March 14, 2005

### **AMENDMENTS TO THE SPECIFICATION**

#### ***In the Specification:***

Please **AMEND** the specification as shown in the following marked up paragraphs, which show changes made relative to the immediate prior version.

Please **AMEND** the paragraph beginning on page 56, line 19 as follows:

The second method to solve the above described problems is that a gate insulating layer is formed through a low-temperature deposition, a semiconductor layer including a lower semiconductor layer on the gate insulating layer and an upper semiconductor layer having a lower higher band gap than that of the lower semiconductor layer, is formed. It will be described in detail with reference to the drawings.

Please **AMEND** the paragraph beginning on page 57, line 7 as follows:

However, a gate insulating layer 60 covering a gate wire 52, 54, and 56 made of insulating material such as organic insulator, amorphous silicon oxide and amorphous silicon nitride is formed through a deposition process of low temperature on an organic insulating layer 40. A semiconductor layer of double-layered structure is formed in an island shape on the gate insulating layer 60 of the gate electrode 56. The semiconductor later 70 includes a lower semiconductor layer 701 made of amorphous silicon on the gate insulating later 60 and an upper semiconductor layer 702 made of amorphous silicon and having a lower higher band gap than that of the lower semiconductor layer 701. The band gap of the lower semiconductor layer 701

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of a thickness of 50-200Å is in a range of 1.9 to 2.1 eV, and the band gap of the upper semiconductor layer 702 of a thickness of 1,000-2,000Å is in the range of 1.7 to 1.8eV in this embodiment.